

Is Now Part of



# **ON Semiconductor**®

# To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="https://www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="https://www.onsemi.com">Fairchild\_questions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized applications, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an equif prese



# FQP10N60C / FQPF10N60C N-Channel QFET<sup>®</sup> MOSFET

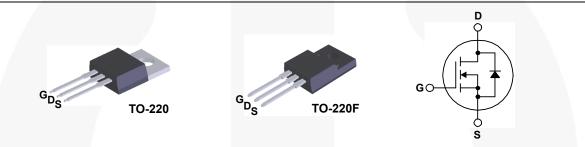
600 V, 9.5 A, 730 mΩ

## Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to mini-mize on-state resistance, provide superior switching perfor-mance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.

### Features

- 9.5 A, 600 V,  $R_{DS(on)}$  = 730 m $\Omega$  (Max.) @ V\_{GS} = 10 V,  $I_{D}$  = 4.75 A
- Low Gate Charge (Typ. 44 nC)
- Low Crss (Typ. 18 pF)
- 100% Avalanche Tested



### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP10N60C	FQPF10N60C	Unit
V <sub>DSS</sub>	Drain-Source Voltage		600		V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		9.5	9.5 *	А
	- Continuous (T <sub>C</sub> =	= 100°C)	5.7	5.7 *	А
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	38	38 *	А
V <sub>GSS</sub>	Gate-Source Voltage		± 30		V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	700		mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	9.5		А
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	15.6		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3		4.5		V/ns
P <sub>D</sub>	Power Dissipation ( $T_c = 25^{\circ}C$ )		156	50	W
	- Derate above 25°C		1.25	0.4	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150		°C
Τ <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300		°C

\* Drain current limited by maximum junction temperature.

### **Thermal Characteristics**

Symbol	Parameter	FQP10N60C	FQPF10N60C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.8	2.5	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5		°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

November 2013

Part Num	ber	Top Mark	Package	Packing Method	Reel S	Size	Tape Wie	dth	Quantity	
FQP10N60C		FQP10N60C	TO-220	Tube	N/A	A	N/A		50 units	
FQPF10N	60C	FQPF10N60C	TO-220F	Tube	N/A	N/A			50 units	
FQPF10N6		FQPF10N60CT	TO-220F				N/A		50 units	
FQPF10N60		FQPF10N60C	TO-220F	Tube	N/A	4	N/A		50 units	
Symbol	Chara	Cteristics T <sub>c</sub> = 25° Parameter	C unless otherwi	Test Conditions	s	Min	Тур	Мах	Uni	
-					_		71	_	_	
Off Character BV <sub>DSS</sub>	1	urce Breakdown Voltage		<sub>s</sub> = 0 V, I <sub>D</sub> = 250 μA		600			V	
ΔBV <sub>DSS</sub> /ΔTJ		vn Voltage Temperature		$V_{GS} = 0.0$ v, $r_D = 250 \ \mu\text{A}$ $I_D = 250 \ \mu\text{A}$ , Referenced to 25°C			0.7		V/°C	
I <sub>DSS</sub>	Zero Gat	e Voltage Drain Current	V <sub>DS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V				1	μA	
			V <sub>DS</sub>	V <sub>DS</sub> = 480 V, T <sub>C</sub> = 125°C				10	μA	
I <sub>GSSF</sub>	Gate-Boo	ly Leakage Current, For	ward V <sub>GS</sub>	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V				100	nA	
I <sub>GSSR</sub>	Gate-Boo	dy Leakage Current, Re	verse V <sub>GS</sub>	$V_{GS}$ = -30 V, $V_{DS}$ = 0 V				-100	nA	
On Character	ristics									
V <sub>GS(th)</sub>	Gate Threshold Voltage		V <sub>DS</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$		2.0		4.0	V	
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance		V <sub>GS</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.75 A			0.6	0.73	Ω	
9 <sub>FS</sub>	Forward Transconductance		V <sub>DS</sub>	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 4.75 A			8.0		S	
Dynamic Cha	racteristio	cs								
C <sub>iss</sub>	Input Capacitance			V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,			1570	2040	pF	
C <sub>oss</sub>	Output C	apacitance	f = 1	f = 1.0 MHz			166	215	pF	
C <sub>rss</sub>	Reverse	Transfer Capacitance					18	24	pF	
Switching Ch	aracterist	ics								
t <sub>d(on)</sub>	1	Delay Time	V <sub>DD</sub>	$V_{DD} = 300 \text{ V}, \text{ I}_{D} = 9.5\text{A},$ $R_{G} = 25 \Omega$ (Note 4)			23	55	ns	
t <sub>r</sub>	Turn-On	Rise Time	R <sub>G</sub>				69	150	ns	
t <sub>d(off)</sub>	Turn-Off	Delay Time					144	300	ns	
t <sub>f</sub>	Turn-Off	Fall Time					77	165	ns	
Q <sub>g</sub>	Total Gat	e Charge		$V_{DS} = 480 \text{ V}, \text{ I}_{D} = 9.5\text{A},$ V_{GS} = 10 V (Note 4)			44	57	nC	
Q <sub>gs</sub>	Gate-Sou	Irce Charge	V <sub>GS</sub>				6.7		nC	
Q <sub>gd</sub>	Gate-Dra	in Charge					18.5		nC	
Drain-Source	Diode Ch	aracteristics and Max	imum Ratin	qs						
I <sub>S</sub>		n Continuous Drain-Sou	,	<u> </u>			-	9.5	Α	
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Cu		rd Current				38	Α		
V <sub>SD</sub>	Drain-So	urce Diode Forward Vol	tage V <sub>GS</sub>	<sub>s</sub> = 0 V, I <sub>S</sub> = 9.5 A				1.4	V	
t <sub>rr</sub>	Reverse	Recovery Time	V <sub>GS</sub>	<sub>s</sub> = 0 V, I <sub>S</sub> = 9.5 A,			420		ns	
Q <sub>rr</sub>	Reverse	Recovery Charge		$dl_F / dt = 100 \text{ A/}\mu\text{s}$			4.2		μC	

1. Repetitive rating: pulse-width limited by maximum junction temperature.

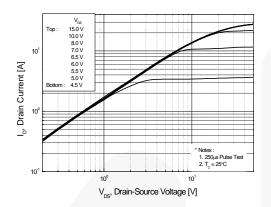
2. L = 14.2 mH, I<sub>AS</sub> = 9.5 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C.

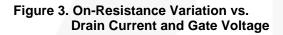
3.  $I_{SD} \leq$  9.5 A, di/dt  $\leq$  200 A/µs,  $V_{DD} \leq BV_{DSS},$  starting  $T_J$  = 25°C.

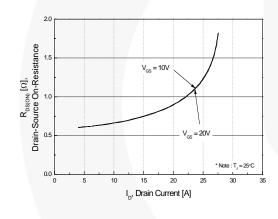
4. Essentially independent of operating temperature typical characteristics.

# **Typical Performance Characteristics**

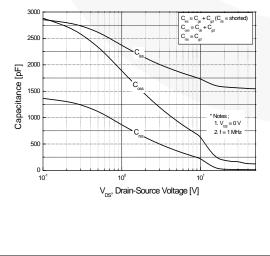


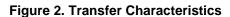


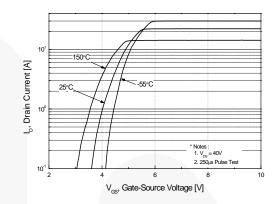




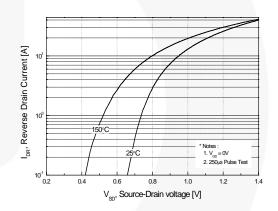




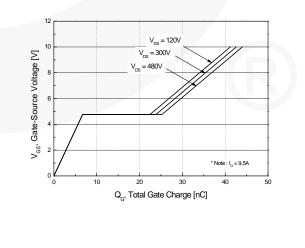


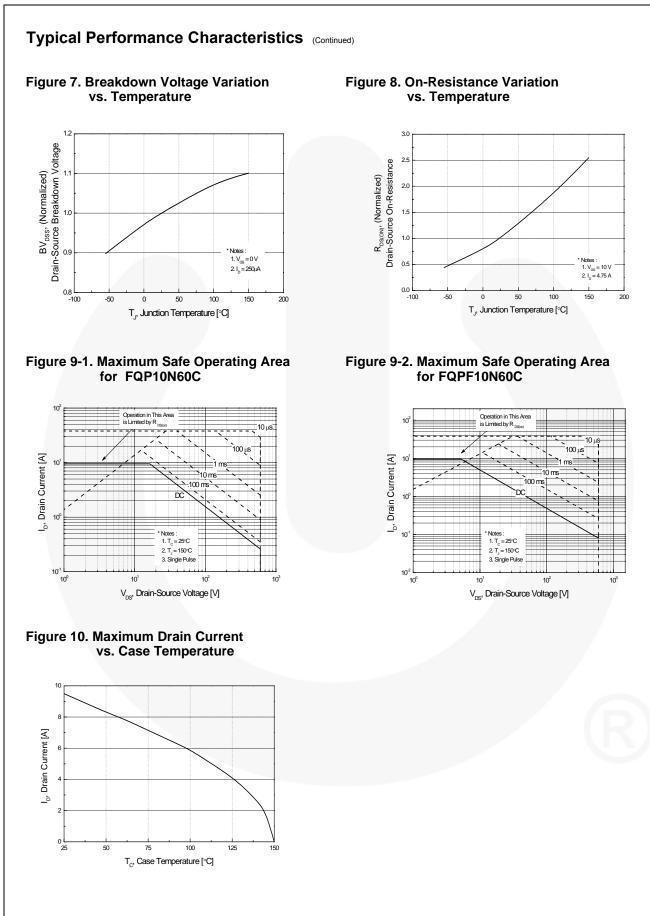








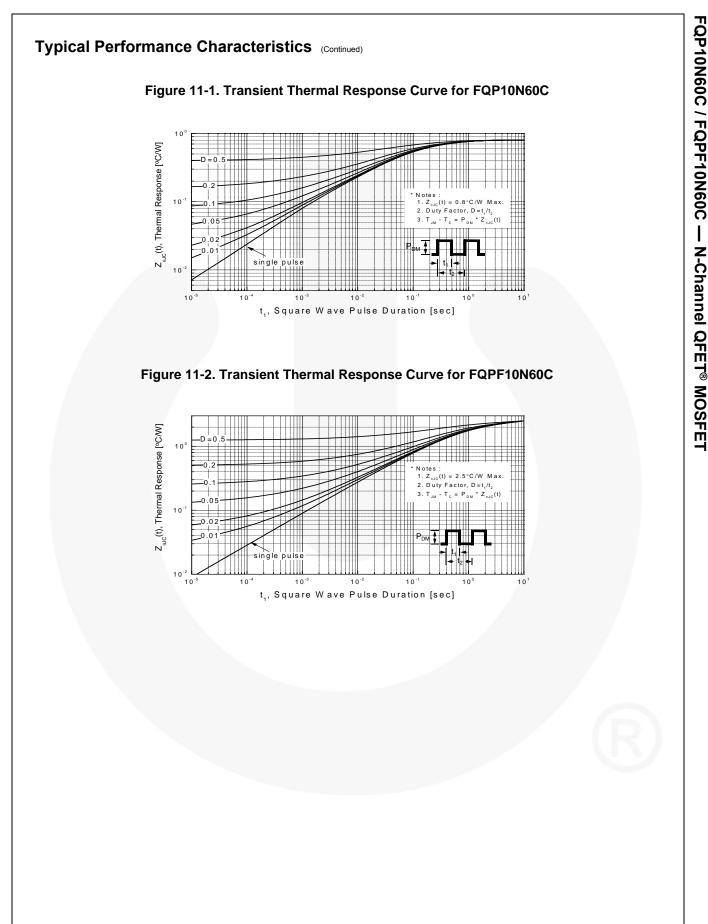


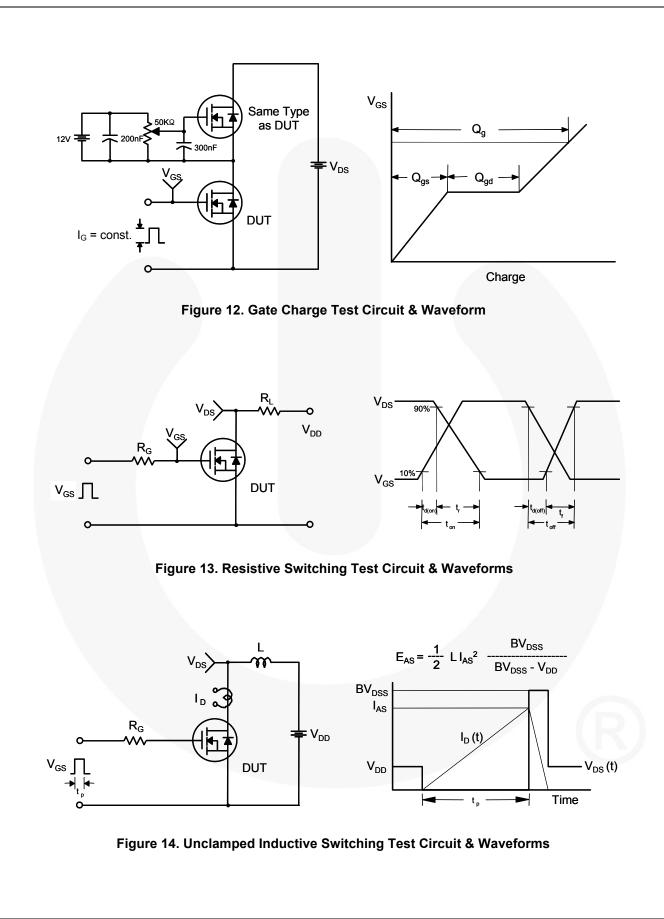


4

©2003 Fairchild Semiconductor Corporation FQP10N60C / FQPF10N60C Rev C1

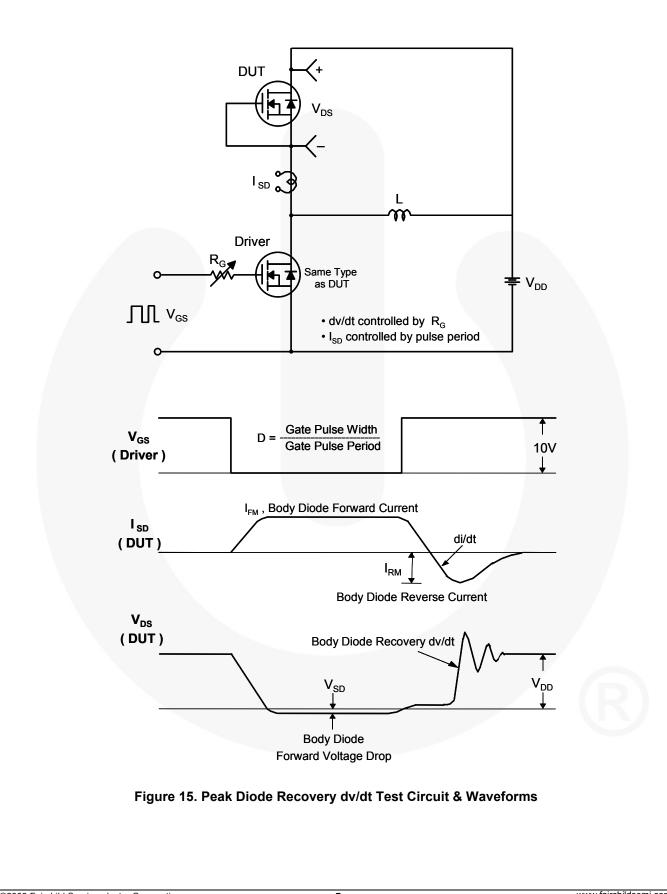
www.fairchildsemi.com

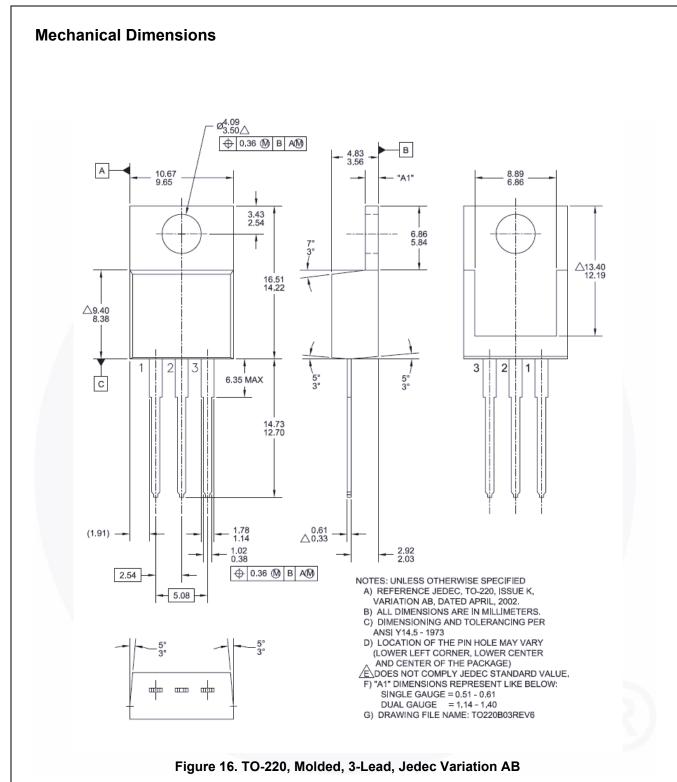




FQP10N60C / FQPF10N60C — N-Channel QFET® MOSFET

6



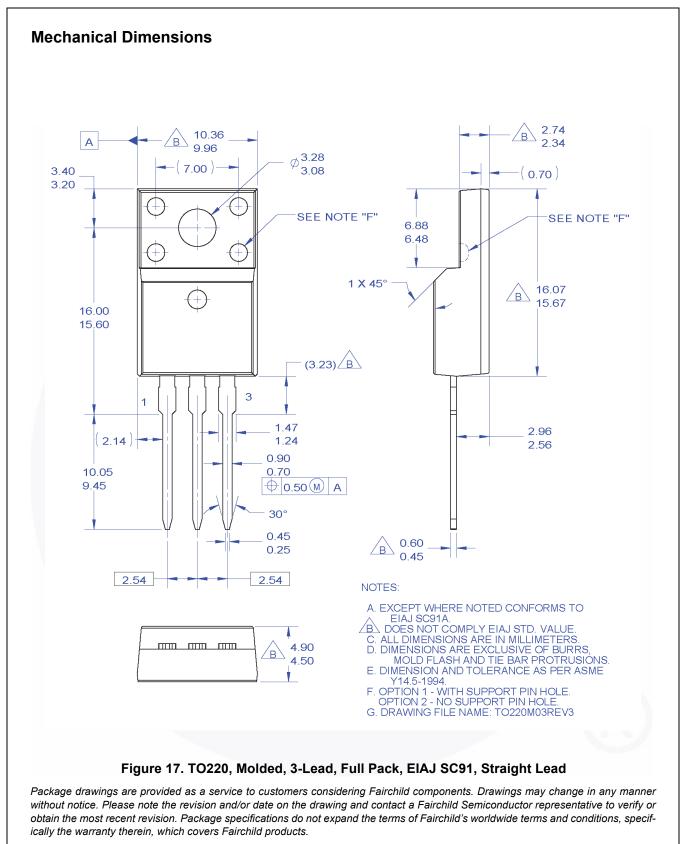


Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TT220-003

FQP10N60C / FQPF10N60C — N-Channel QFET<sup>®</sup> MOSFET



Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TF220-003

FQP10N60C / FQPF10N60C — N-Channel QFET<sup>®</sup> MOSFET



SEMICONDUCTOR

#### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks

intended to be an exhaustive list of	all such li auemarks.		
AccuPower™	F-PFS™		Sync-Lock™
AX-CAP <sup>®</sup> *	FRFET®		SYSTEM ®*
BitSiC™	Global Power Resource <sup>SM</sup>	PowerTrench <sup>®</sup>	GENERAL
Build it Now™	GreenBridge™	PowerXS™	TinyBoost <sup>®</sup>
CorePLUS™	Green FPS™	Programmable Active Droop™	TinyBuck <sup>®</sup>
CorePOWER™	Green FPS™ e-Series™	QFET®	TinyCalc™
CROSSVOLT™	G <i>max</i> ™	QS™	TinyLogic®
CTL™	GTO™	Quiet Series™	TINYOPTO™
Current Transfer Logic™	IntelliMAX™	RapidConfigure™	TinyPower™
DEUXPEED®	ISOPLANAR™		TinyPWM™
Dual Cool™	Marking Small Speakers Sound Lou		TinyWire™
EcoSPARK <sup>®</sup>	and Better™	Saving our world, 1mW/W/kW at a time™	TranSiC™
EfficentMax™	MegaBuck™	SignalWise™	TriFault Detect™
ESBC™	MICROCOUPLER™	SmartMax™	TRUECURRENT®*
<b>F</b> B	MicroFET™	SMART START™	µSerDes™
T .	MicroPak™	Solutions for Your Success™	
Fairchild <sup>®</sup>	MicroPak2™	SPM <sup>®</sup>	SerDes <sup>™</sup>
Fairchild Semiconductor <sup>®</sup>	MillerDrive™	STEALTH™	UHC®
FACT Quiet Series™	MotionMax™	SuperFET®	Ultra FRFET™
FACT®	mWSaver®	SuperSOT™-3	UniFET™
FAST®	OptoHiT™ OptoAlon®	SuperSOT™-6	VCX™
FastvCore™	OPTOLOGIC <sup>®</sup> OPTOPLANAR <sup>®</sup>	SuperSOT™-8	VisualMax™
FETBench™	OPTOPLANAR*	SupreMOS®	VoltagePlus™
FPS™		SyncFET™	XS™

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly ori indirectly, any claim of personal injury or death

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi: FQPF10N60C\_F105